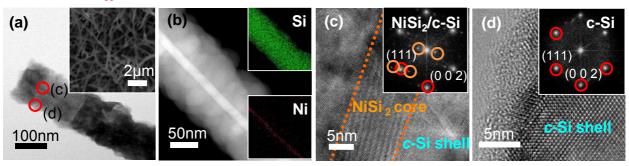
## Supporting Information for "Kinetics-Driven High Power Li-ion Battery with *a*-Si/NiSi<sub>x</sub> Core-Shell Nanowire Anodes"

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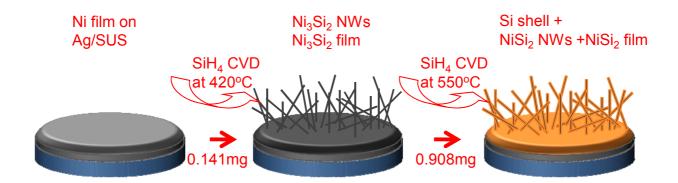
## c-Si/NiSix NWs



**Figure S1** (a) TEM image of an individual c-Si /NiSi<sub>x</sub> NW. The inset shows a plan-view SEM image of c-Si/NiSi<sub>x</sub> NW grown on SUS substrate. (b) HAADF image of a c-Si/NiSi<sub>x</sub> NW and EDX elemental mapping images (inset). (c) HRTEM image of an individual c-Si/NiSi<sub>x</sub> NW at the core region and the corresponding FFT-DP along the [1-10] zone axis (inset). The spot in orange color circle arise from the interface-twin boundary between c-Si and NiSi<sub>2</sub> (d) HRTEM image of an individual c-Si/NiSi<sub>x</sub> NW at the shell region and the corresponding FFT-DP along the [1-10] zone axis (inset).



**Figure S2** A photograph of the a-Si/NiSi<sub>x</sub> NW grown on the whole SUS substrate of 15  $\Phi$  diameter.

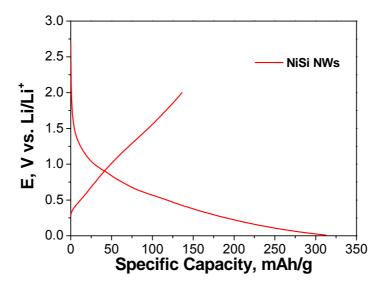


- Phase of Ni-silicide after SiH<sub>4</sub> reactions
- SiH<sub>4</sub> CVD on Ni at 420°C→ Ni<sub>3</sub>Si<sub>2</sub> NWs and Ni<sub>3</sub>Si<sub>2</sub> film
- SiH<sub>4</sub> CVD on Ni<sub>3</sub>Si<sub>2</sub> NWs and Ni<sub>3</sub>Si<sub>2</sub> film at 550°C → Si Shell, NiSi<sub>2</sub> NWs and NiSi<sub>2</sub> film
- Average mass change
- SiH<sub>4</sub> CVD on Ni film at 420°C for Ni<sub>3</sub>Si<sub>2</sub> NW growth: 0.141mg
- SiH<sub>4</sub> CVD on Ni<sub>3</sub>Si<sub>2</sub> NWs and Ni<sub>3</sub>Si<sub>2</sub> film at 550°C for Si shell deposition: 0.908mg
- Additional mass due to phase transition
   Ni → Ni<sub>3</sub>Si<sub>2</sub> NWs + Ni<sub>3</sub>Si<sub>2</sub> film : 0.141mg
   From this result estimated additional mass due to phase transition
   Ni<sub>3</sub>Si<sub>2</sub> NWs + Ni<sub>3</sub>Si<sub>2</sub> film → NiSi<sub>2</sub> NWs + NiSi<sub>2</sub> film : 0.282mg
- Mass calculation of the Si Shell
   0.908mg = Si Shell + additional mass due to phase transition + other silicide reaction

Phase transition mass from  $\mathrm{Ni_3Si_2}$  to  $\mathrm{NiSi_2}$  is 0.282mg, Therefore mass of Si shell is 0.626mg

We finally normalized the specific capacity of Si/Ni-silicide NW anode using the mean value of the expected mass of Si shell, 0.626mg.

**Figure S3** Explanation of the normalization method for calculating the gravimetric capacity.



**Figure S4** The current charge/discharge curve for the 1<sup>st</sup> cycle of the NiSi<sub>x</sub> NW cell in the galvanostatic mode.